

Standard Rectifier Module

$$V_{RRM} = 2 \times 800 \text{ V}$$

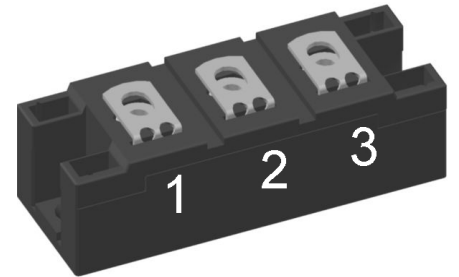
$$I_{FAV} = 165 \text{ A}$$

$$V_F = 1.05 \text{ V}$$

Phase leg

Part number

MDD142-08N1



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage				900	V	
V_{RRM}	max. repetitive reverse blocking voltage				800	V	
I_R	reverse current	$V_R = 800\text{ V}$			1	mA	
		$V_R = 800\text{ V}$			20	mA	
V_F	forward voltage drop	$I_F = 150\text{ A}$			1.12	V	
		$I_F = 300\text{ A}$			1.30	V	
		$I_F = 150\text{ A}$			1.05	V	
		$I_F = 300\text{ A}$			1.26	V	
I_{FAV}	average forward current	$T_C = 100^\circ\text{C}$			165	A	
$I_{F(RMS)}$	RMS forward current	180° sine			300	A	
V_{F0}	threshold voltage	} for power loss calculation only			0.80	V	
r_F	slope resistance				1.3	mΩ	
R_{thJC}	thermal resistance junction to case				0.21	K/W	
R_{thCH}	thermal resistance case to heatsink			0.08		K/W	
P_{tot}	total power dissipation				600	W	
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine			4.70	kA	
		t = 8,3 ms; (60 Hz), sine			5.08	kA	
		t = 10 ms; (50 Hz), sine			4.00	kA	
		t = 8,3 ms; (60 Hz), sine			4.32	kA	
I^2t	value for fusing	t = 10 ms; (50 Hz), sine			110.5	kA ² s	
		t = 8,3 ms; (60 Hz), sine			107.1	kA ² s	
		t = 10 ms; (50 Hz), sine			79.8	kA ² s	
		t = 8,3 ms; (60 Hz), sine			77.5	kA ² s	
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$		238		pF	



Package Y4				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			300	A	
T_{VJ}	virtual junction temperature		-40		150	°C	
T_{op}	operation temperature		-40		125	°C	
T_{stg}	storage temperature		-40		125	°C	
Weight					150	g	
M_D	mounting torque		2.25		2.75	Nm	
M_T	terminal torque		4.5		5.5	Nm	
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
V_{ISOL}	isolation voltage	t = 1 second			3600	V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3000	V	



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD142-08N1	MDD142-08N1	Box	6	430641

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$



Rectifier

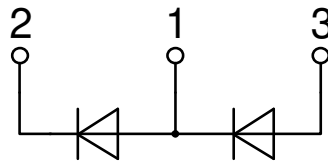
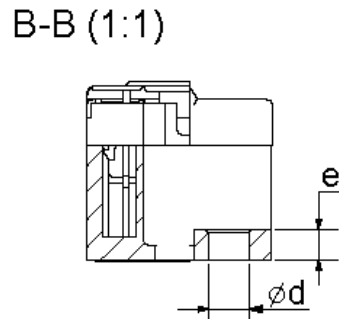
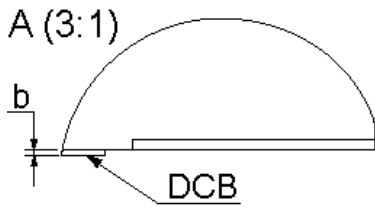
$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	0.7	mΩ



Outlines Y4



Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	





Rectifier

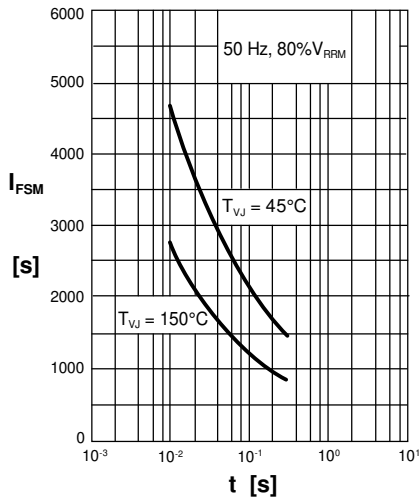


Fig. 1 Surge overload current
 I_{FSM} : Crest value, t : duration

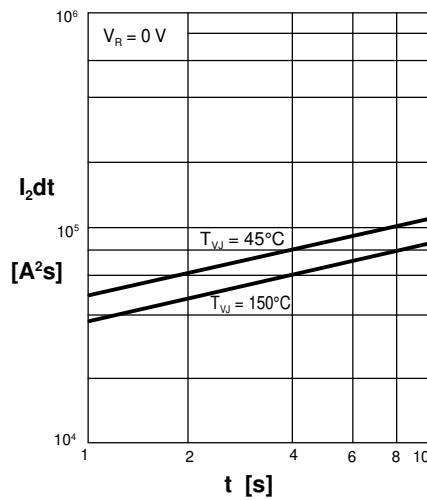


Fig. 2 I^2dt versus time (1-10 ms)

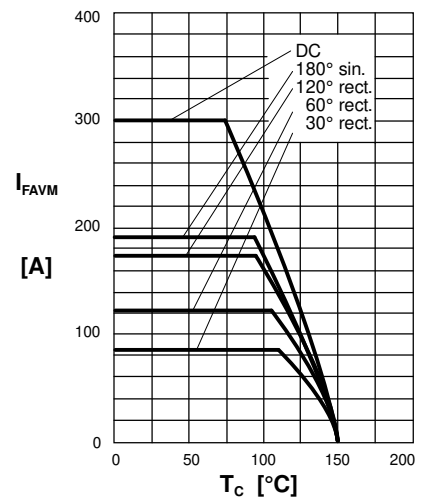


Fig. 2a Maximum forward current at case temperature

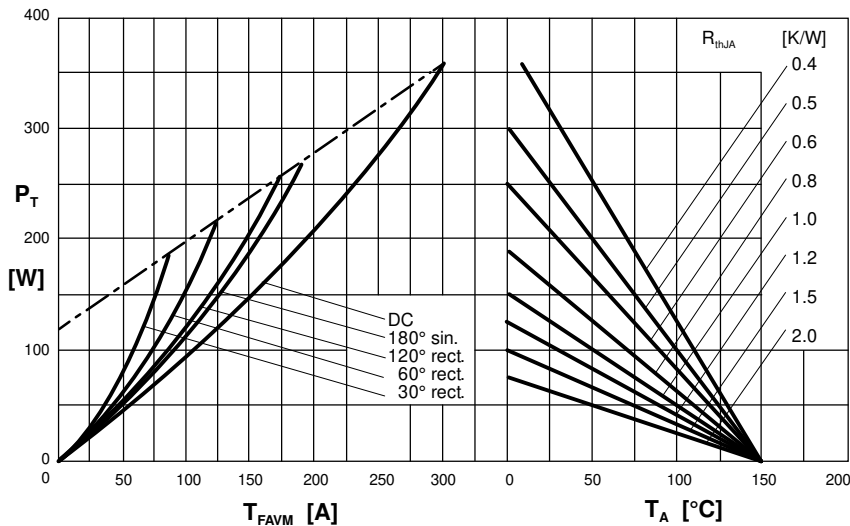


Fig. 3 Power dissipation vs. forward current and ambient temperature (per diode)

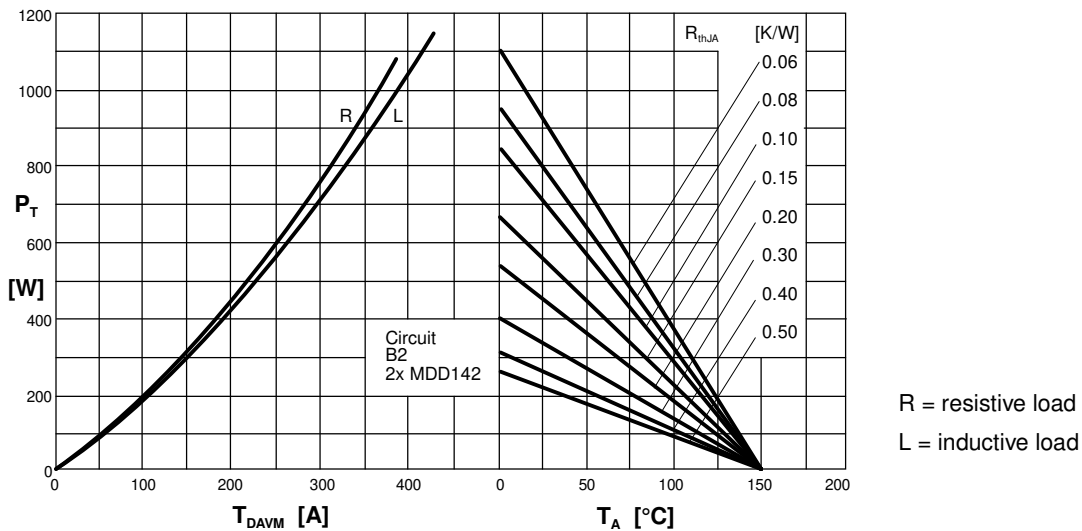


Fig. 4 Single phase rectifier bridge: Power dissipation vs. direct output current and ambient



Rectifier

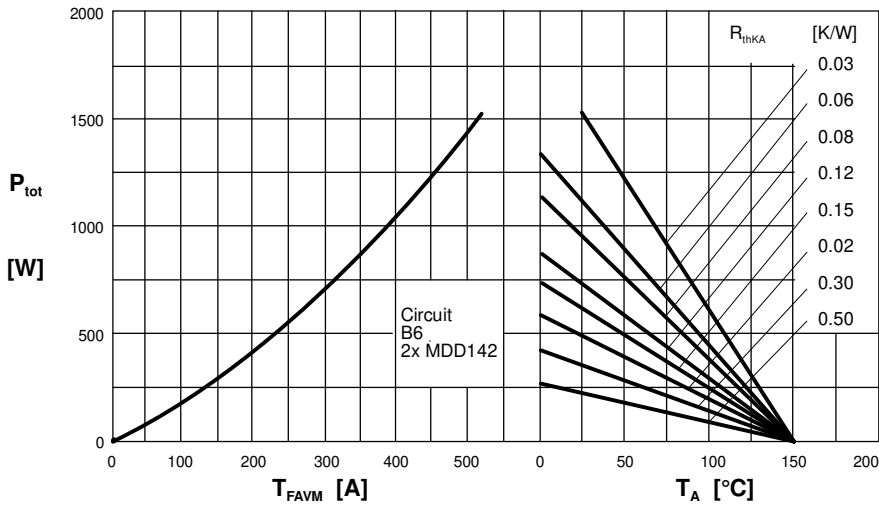


Fig. 5 Three phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature

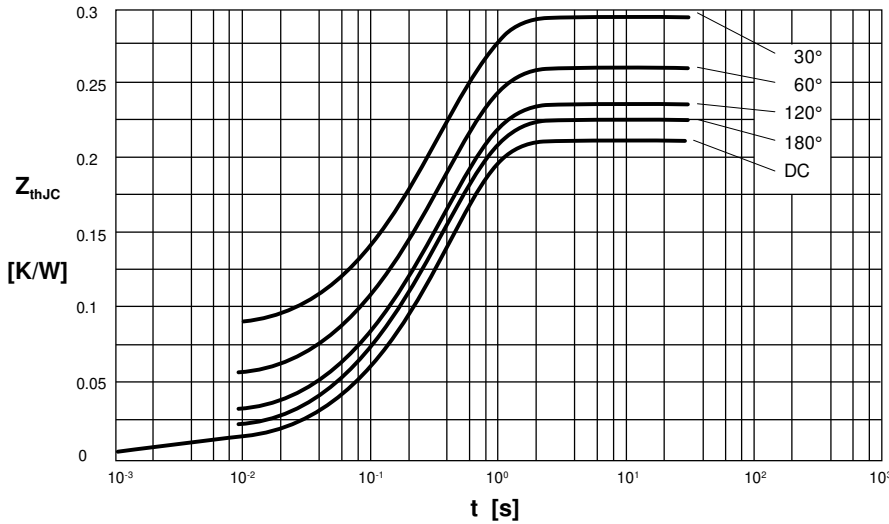


Fig. 6 Transient thermal impedance junction to case (per diode)

R_{thJC} for various conduction angles d :

d	R_{thJC} [K/W]
DC	0.210
180°	0.223
120°	0.233
60°	0.260
30°	0.295

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0087	0.001
2	0.0163	0.065
3	0.1850	0.400

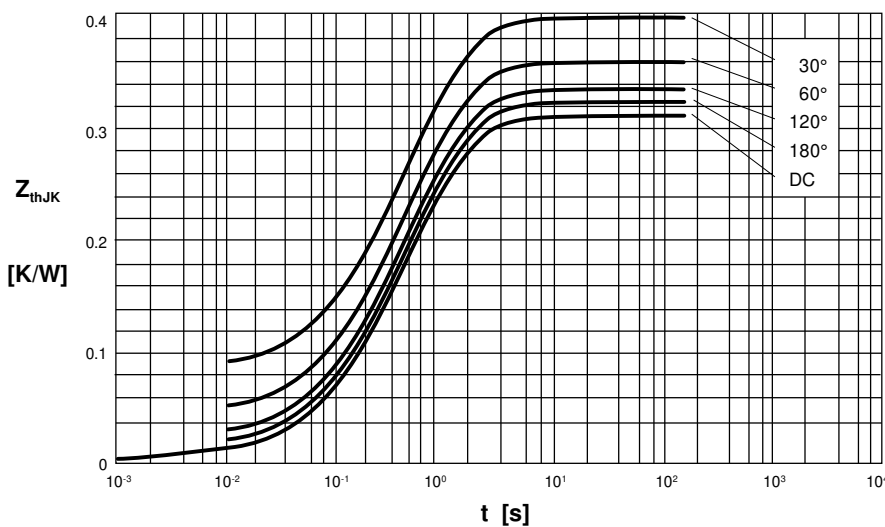


Fig. 7 Transient thermal impedance junction to heatsink (per diode)

R_{thJK} for various conduction angles d :

d	R_{thJK} [K/W]
DC	0.310
180°	0.323
120°	0.333
60°	0.360
30°	0.395

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0087	0.001
2	0.0163	0.065
3	0.1850	0.400
4	0.1000	1.290